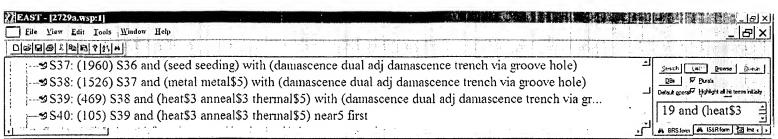
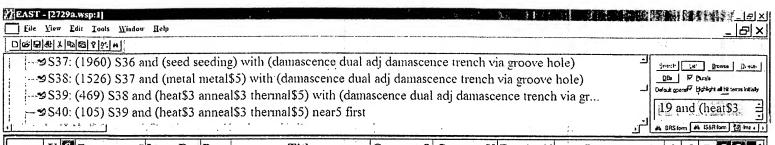


	U	1	Do	cument I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3
1	R	Г	US	2005009	2005050	30	Semiconductor device an	438/637			Kunishima, Hiroyuk	٢	٢	г	Г	ГГ
2	P	Г	US	2005008	2005042	114	Revolution member supp	204/297.0	204/297.08		Hongo, Akihisa et a	Г	Г	Г	г	ГГ
3	P	Г	US	2005004	2005030	19	Chip stack package and	257/678	257/686;		Lee, Kang-Wook et	Г	Г	r.	г	ГГ
4	F	Г	US	2005000	2005011	.10	Semiconductor memory d	257/295		in departure for the Assembles of the September 1921 1 1 1	Okuno, Yasutoshi	Г	Γ.	г	Г	rr
5	Þ	ŗ	US	2004020	2004102	78	Integrated equipment set	204/229.8	257/E21.5		Li, Hongwen et al.	Г.	٣	r	r	r r
6	F	ŗ	US	2004019	2004100	8	Method for forming thick	438/692			Wang, Sung-Hsiung	٦	Г	Г	r	ГГ
7	P	r	US	2004005	2004031	14	Dopant interface formatio	438/162	257/E21.1		Dublin, Valery M. e	г	Г	٦	г	гг
8	ᄝ	Г	US	2004005	2004031	14	Dopant interface formatio	438/106	257/E21.1		Dubin, Valery M. et	г	г	г	г	Г
9	₽	Г	US	2004001	2004012	31	Semiconductor device an	438/637			Kunishima, Hiroyuk	r	Г	٦	Г	ГГ
10	P	٦	US	2004000	2004011	75	Integrated equipment set	156/345.1	257/E21.5	ang taum anumum unu magnumm pi in ipig si	Pan, Judon Tony et	Г	٦	7	r	r r
11	P	ŗ	US	2003020	2003103		Semiconductor device an	257/750	257/762;	A MARKATON AS AND THE REAL PROPERTY AND ADDRESS AS A SECOND	Ueno, Kazuyoshi					Г Г
12	P	r.	US	2003016	2003090	1	Identifying defects in a co	374/5	374/7		Borden, Peter G. et	Г	г	r.	r	ГГ
13	P	Г.	US	2003007	2003041	42	Integrated equipment set	700/121	257/E21.1	- Mandrick in the Mandrick and a specific color in	Cheung, Robin W.	г	Г	r	٦	ГГ
14	Þ	ŗ	US	2003005	2003032	29	Method and apparatus fo	266/81	266/250	And the real parties of the second second	Weaver, Robert A.	Г	Г	Г	7	r r
15	ᄝ	r	US	2003001	2003011	30	Locally increasing sidewa	438/639	257/E21.2		Apelgren, Eric M. e	٢	Г	г	г	г г
16	F	г	US	2003001	2003011	17	Method for manufacturin	204/298.1	257/E21.1		Ueno, Kazuyoshi	Г	г	г	г	г г
17	₽.	Г	US	2002007	2002062	19	Method and apparatus fo	205/157	204/274;		Ritzdorf, Thomas L.	г	Г	Г	г	r r
18	P.	٢	US	2002007	2002061	22	Method of enhancing adh	438/629	257/E21.2							r r :
19	P	Г	US	2002003	2002032	23	Method and apparatus fo	438/618	257/E21.5	and the treatments are the department, the Reyards of	Ritzdorf, Thomas L.	Γ.	г	7	Ľ	ГГ
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12	Þ	гUS	2003016	2003090		Identifying defects in a co	374/5	374/7		Borden, Peter G. et	г		г	r	ריר
13	P	гUS	2003007	2003041 4	2	Integrated equipment set	700/121	257/E21.1		Cheung, Robin W.	٣	Г	г	r	ГГ
14	P	гUS	2003005	2003032 2	9	Method and apparatus fo	266/81	266/250		Weaver, Robert A.	г	Г	г	r	гг
15	P	гUS	2003001	2003011 3	0	Locally increasing sidewa	438/639	257/E21.2		Apelgren, Eric M. e	г	Г	г	c	ГГ
16	F	r US	2003001	2003011 1	7	Method for manufacturin	204/298.1	257/E21.1		Ueno, Kazuyoshi	г	г	г	r	ГГ
17	P	гÜS	2002007	2002062 1	9	Method and apparatus fo	205/157	204/274;		Ritzdorf, Thomas L.	г	г	г	r	Γ¦Γ
18	F	r US	2002007	2002061 2	2	Method of enhancing adh	438/629	257/E21.2		Gilbert, Stephen R.	г	г	г	Г	гГ
19	P	r US	2002003	2002032 2	3	Method and apparatus fo	438/618	257/E21.5		Ritzdorf, Thomas L.	г	г	г	Г	гіг
20	P.	r US	2002000	2002011 2	1	Hydrogen-free contact et	438/3	257/E21.0		Ma, Shawming et al	г	٦	Г	-	гг
21	Þ	r US	2002000	2002010 1	9	METHOD AND APPAR	148/518	148/536;		RITZDORF, THOM	٦	· r	г	Г	гіг
22 .	P	гUS	2001005	2001121 3	0	Dielectric formation to se	438/597	257/E21.5		Besser, Paul R. et al	г	, r	г	г	гг
23	Þ	r US	2001004	2001112 2	2	Method of planarizing a c	438/653 -	257/E21.3		Gilbert, Stephen R.	г	Е	г	E	г г-
24	P	гUS	2001003	2001110 3	4	Liquid treatment system a	118/70			Nakashima, Satoshi	г	г	Г	Г	ГГ
25	Þ	гUS	2001003	2001102 1	3	Semiconductor device ma	438/687 🗩	257/E21.1		Yamasaki, Hideaki e	г	г	г	г	Г.Г.
26	P	r US	2001003	2001102 2	2	Hardmask designs for dry	438/396 .	257/E21.0		Moise, Theodore et	г	Г	г	г	г г.
27	P	гUS	2001002	2001092 8	9	Semiconductor substrate	427/346	156/345.12		Kimura, Norio et al.	г	г	Г	г	г г.
28	Þ	гUS	6861027	2005030 3	0	Method and apparatus fo	266/256	118/725	1	Weaver; Robert A.	г	Г.	Г	г	г.,г
29	Þ	гUS	6841458	2005011 1	3	Dopant interface formation	438/510	257/E21.1		Dubin; Valery M. et	г	Г	г	г	
30				2004062 1		Method for filling recesse		205/157;	dental de la companie	Ritzdorf, Thomas L.	Г	г	Г.	г	ГГ
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31	P	г	US 6635528	2003102 22	Method of planarizing a c	438/253	257/E21.3	:	Gilbert; Stephen R.	r	٦	٦	г	r ; r
32	P	Г	US 6634370	2003102 32	Liquid treatment system a	134/61	118/500;	1	Nakashima; Satoshi	Γ,	г	Г	Г	r r
33	P	٦	US 6610594	2003082 29	Locally increasing sidewa	438/629	257/E21.2	i :	Apelgren; Eric M. e	г	г	г.	r	гГг
34	P	Г	US 6576546	2003061 21	Method of enhancing adh	438/629	257/E21.2		Gilbert; Stephen R.	۲	г	Г.	E	ר [ר
35	F	Г	US 6548343	2003041 18	Method of fabricating a f	438/240	438/250;	·	Summerfelt; Scott	٦	Г	Г	r	r r
36	F	ī	US 6534809	2003031 22	Hardmask designs for dry	257/295	257/751;	1	Moise; Theodore et	Г	г	Г	E	r r
37	₽	r	US 6514844	2003020 29	Sidewall treatment for lo	438/597	257/E21.2		Martin; Jeremy I. et	г	г	г	Г	r [r
38	F	ī	US 6508920	2003012 20	Apparatus for low-temper	204/194	118/58;	: : :	Ritzdorf; Thomas L.	г	г	r.	Е	ב ְר
39	F	Г	US 6492222	2002121 19	Method of dry etching PZ	438/240	438/239;	1 1	Xing; Guoqiang	Г	٦	г	Γ	רוֹר
40	Þ.	Ī	US 6486063	2002112 13	Semiconductor device ma	438/687	257/E21.1	de » « « « « » « » « » « » « » « » « » «	Yamasaki; Hideaki	г	г	Г	7	г [†] г
41	Þ	Г	US 6485988	2002112 21	Hydrogen-free contact et	438/3	257/E21.0	1 1	Ma; Shawming et al	г	г	Г.	Г	ריר
42	P	[US 6482656	2002111 21	Method of electrochemic	438/2	257/E21.1		Lopatin; Sergey	г	г	г	r	r
43	F	Ī	US 6478935	2002111 16	Semiconductor device pla	204/237	118/44;	frames unamas amas a	Ueno; Kazuyoshi	٦	Г	Г	г	Г;Г
44	P	-	US 6471913	2002102 30	Method and apparatus fo	266/256	118/725;	1	Weaver; Robert A.	٦	Г	г	7	r ; r
45	₽	-	US 6445070	2002090 9	Coherent carbide diffusio	257/751	257/759;		Wang; Pin-Chin Co	٦	г	г	F	r , r
46	P	-	US 6368967	2002040 31	Method to control mecha	438/687 🗸	257/E21.5	!	Besser; Paul R.	Г	Г	٦	г	г
47	₽	[US 6303486	2001101 29	Method of fabricating co	438/618	257/374;	1 1 2 4	Park; Stephen Keet	г	r.	<u></u>	E	Г
48	Þ	Г	US 6261963	2001071 17	Reverse electroplating of	438/704	205/640;	I	Zhao; Larry et al.	г	٦	٦	г	C C
49	٦	r	US 6221765	2001042 17	Method for manufacturin	438/653	257/E21.1		Ueno; Kazuyoshi	Þ	Г	Г	г	ГГ
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